

HALF-BRIDGE DRIVER

Features

- Floating channel designed for bootstrap operation Fully operational to +600V
 Tolerant to negative transient voltage dV/dt immune
- Gate drive supply range from 10 to 20V
- Undervoltage lockout for both channels
- 3.3V, 5V and 15V input logic compatible
- Cross-conduction prevention logic
- Matched propagation delay for both channels
- High side output in phase with IN input
- Logic and power ground +/- 5V offset.
- Internal 500ns dead-time, and programmable up to 5us with one external R_{DT} resistor
- Lower di/dt gate driver for better noise immunity
- The dual function DT/SD pin input turns off both channels.
- Available in Lead-Free

Description

The IR21091(S) are high voltage, high speed power MOSFET and IGBT drivers with dependant high and low side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable rugge-

Product Summary

VOFFSET 600V max.

I_{O+}/- 120 mA / 250 mA

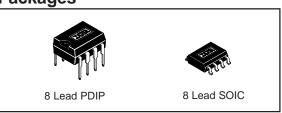
VOUT 10 - 20V

ton/off (typ.) 680 & 170 ns

Dead time 500 ns

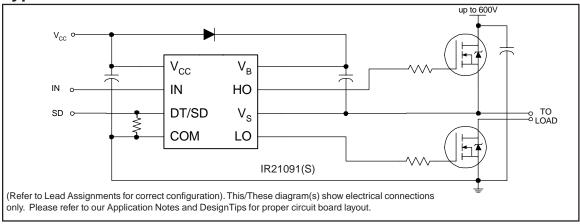
(programmable up to 5uS)

Packages



dized monolithic construction. The logic input is compatible with standard CMOS or LSTTL output, down to 3.3V logic. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high side configuration which operates up to 600 volts.

Typical Connection



International

TOR Rectifier

Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition		Min.	Max.	Units
V _B	High side floating absolute voltage		-0.3	625	
Vs	High side floating supply offset voltage		V _B - 25	V _B + 0.3	
V _{HO}	High side floating output voltage		V _S - 0.3	V _B + 0.3	
Vcc	Low side and logic fixed supply voltage		-0.3	25] _v
V _{LO}	Low side output voltage		-0.3	V _{CC} + 0.3] V
DT/SD	Programmable dead-time and shut-down pin voltage		V _{SS} - 0.3	V _{CC} + 0.3	
V _{IN}	Logic input voltage		V _{SS} - 0.3	V _{CC} + 0.3	
dV _S /dt	Allowable offset supply voltage transient		_	50	V/ns
PD	Package power dissipation @ T _A ≤ +25°C	(8 Lead PDIP)	_	1.0	
		(8 Lead SOIC)	_	0.625	W
Rth _{JA}	Thermal resistance, junction to ambient	(8 Lead PDIP)	_	125	°C/W
		(8 Lead SOIC)	_	200	C/VV
TJ	Junction temperature		_	150	
T _S	Storage temperature		-50	150	°C
TL	Lead temperature (soldering, 10 seconds)		_	300	

Recommended Operating Conditions

The input/output logic timing diagram is shown in figure 1. For proper operation the device should be used within the recommended conditions. The V_S offset rating are tested with all supplies biased at 15V differential.

Symbol	Definition	Min.	Max.	Units
VB	High side floating supply absolute voltage	V _S + 10	V _S + 20	
Vs	High side floating supply offset voltage	Note 1	600	
VHO	High side floating output voltage	Vs	V _B	
Vcc	Low side and logic fixed supply voltage	10	20	V
V _{LO}	Low side output voltage	0	Vcc	, v
VIN	Logic input voltage	V _{SS}	Vcc	
DT/SD	Programmable dead-time and shut-down pin voltage	V _{SS}	V _{CC}	
TA	Ambient temperature	-40	125	°C

Note 1: Logic operational for V_S of -5 to +600V. Logic state held for V_S of -5V to -V_{BS}. (Please refer to the Design Tip DT97-3 for more details).

Dynamic Electrical Characteristics

 V_{BIAS} (V_{CC} , V_{BS}) = 15V, C_L = 1000 pF, T_A = 25°C, DT = VSS unless otherwise specified.

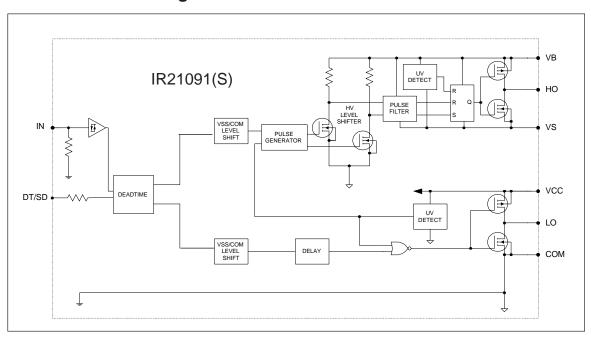
Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions	
ton	Turn-on propagation delay	_	750	950		V _S = 0V	
toff	Turn-off propagation delay	_	200	280		V _S = 0V or 600V	
MT	Delay matching, HS & LS turn-on/off	_	0	70			
t _r	Turn-on rise time	_	150	220		V _S = 0V	
tf	Turn-off fall time	_	50	80		V _S = 0V	
DT	Deadtime: LO turn-off to HO turn-on(DTLO-HO) &	400	540	680		RDT= 0	
	HO turn-off to LO turn-on (DTHO-LO)	4	5	6	usec	RDT = 200k	
MDT	Deadtime matching = DTLO - HO - DTHO-LO	_	0	60		RDT=0	
		_	0	600		RDT = 200k	
tsd	Shut down propagation delay	215	_	615			

Static Electrical Characteristics

 V_{BIAS} (V_{CC} , V_{BS}) = 15V, DT= V_{SS} and T_A = 25°C unless otherwise specified. The V_{IL} , V_{IH} and I_{IN} parameters are referenced to V_{SS} /COM and are applicable to the respective input leads: IN and DT. The V_O , I_O and Ron parameters are referenced to COM and are applicable to the respective output leads: HO and LO.

Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
V _{IH}	Logic "1" input voltage for HO & logic "0" for LO	2.9	_	_		V _{CC} = 10V to 20V
V _{IL}	Logic "0" input voltage for HO & logic "1" for LO	_	_	0.8		V _{CC} = 10V to 20V
V _{SD,TH}	DT/SD pin shutdown input threshold	11.5	13	14.5		
VoH	High level output voltage, V _{BIAS} - V _O	_	0.8	1.4		I _O = 20 mA
V _{OL}	Low level output voltage, VO	_	0.3	0.6		I _O = 20 mA
I _{LK}	Offset supply leakage current	_	_	50	μА	$V_{B} = V_{S} = 600V$
I _{QBS}	Quiescent V _{BS} supply current	20	60	150	μΑ	V _{IN} = 0V or 5V
IQCC	Quiescent V _{CC} supply current	0.4	1.0	1.6	mA	V _{IN} = 0V or 5V
						RDT = 0
I _{IN+}	Logic "1" input bias current	_	5	20	μΑ	IN = 5V, SD = 0V
I _{IN} -	Logic "0" input bias current	_	1	2	μΛ	$IN = 0V, \overline{SD} = 5V$
V _{CCUV+}	V _{CC} and V _{BS} supply undervoltage positive going	8.0	8.9	9.8		
V _{BSUV+}	threshold					
V _{CCUV} -	V _{CC} and V _{BS} supply undervoltage negative going	7.4	8.2	9.0		
V _{BSUV} -	threshold					
VCCUVH	Hysteresis	0.3	0.7	_		
V _{BSUVH}						
I _{O+}	Output high short circuit pulsed vurrent	120	200	_	Л	$V_O = 0V$, $PW \le 10 \mu s$
I _O -	Output low short circuit pulsed current	250	350	_	mA	$V_O = 15V,PW \le 10 \mu s$

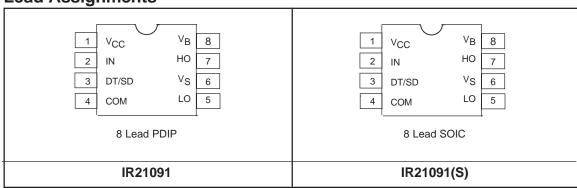
Functional Block Diagrams



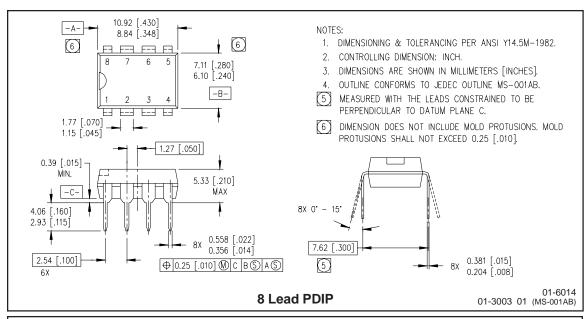
Lead Definitions

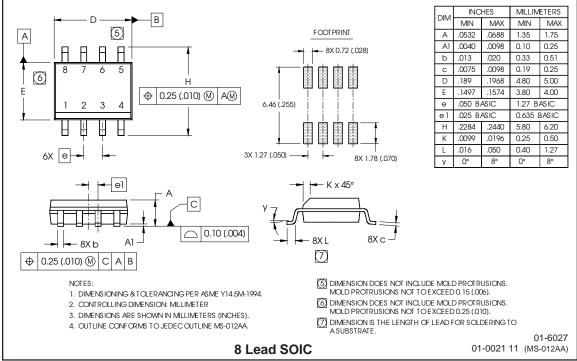
Symbol	Description			
IN	Logic input for high and low side gate driver outputs (HO and LO), in phase with HO			
DT/SD	Programmable dead-time lead, referenced to VSS. Disables input/output logic when tied to VCC			
V _B	High side floating supply			
НО	High side gate drive output			
Vs	High side floating supply return			
Vcc	Low side and logic fixed supply			
LO	Low side gate drive output			
COM	Low side return			

Lead Assignments



Case Outlines





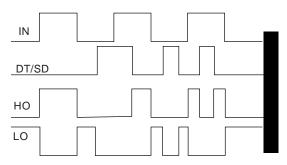


Figure 1. Input/Output Timing Diagram

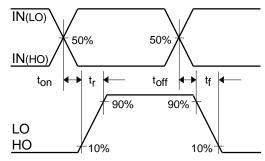


Figure 2. Switching Time Waveform Definitions

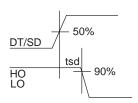


Figure 3. Shutdown Waveform Definitions

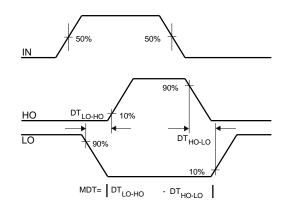


Figure 4. Deadtime Waveform Definitions

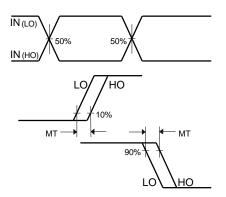
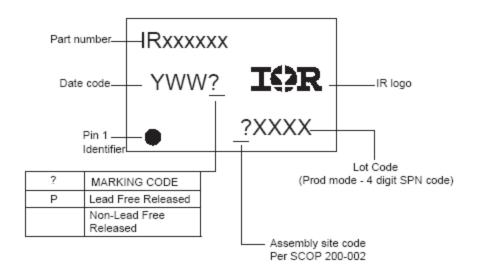


Figure 5. Delay Matching Waveform Definitions

LEADFREE PART MARKING INFORMATION



Basic Part (Non-Lead Free)

Lead-Free Part

8-Lead PDIP IR21091 order IR21091 8-Lead SOIC IR21091S order IR21091S 8-Lead PDIP IR21091 order IR21091PBF 8-Lead SOIC IR21091S order IR21091SPBF



This product has been designed and qualified for the Industrial market.

Qualification Standards can be found on IR's Website.

Data and specifications subject to change without notice.

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